

Fig.1 SEM images of Mo films deposited on Si by (a) MoF₆ or (b) F4M.

Damage to Si when Mo films are deposited by MoF₆, no damage when F4M is used.

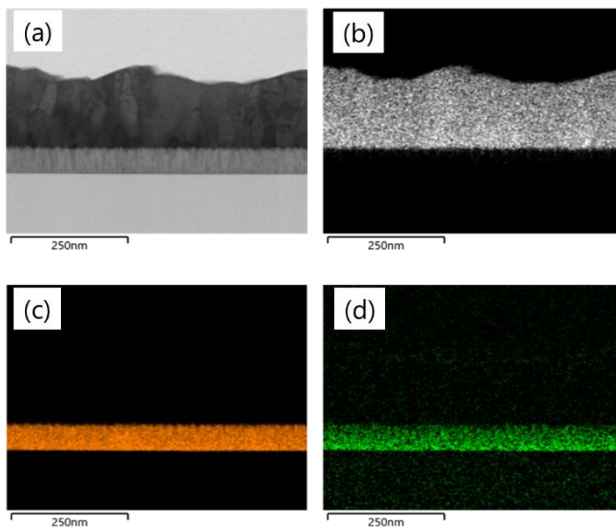


Fig. 2 (a) STEM images of Mo films deposited on TiN by F4M ; EDX elemental mapping for (b) Mo, (c) Ti and (d) N.

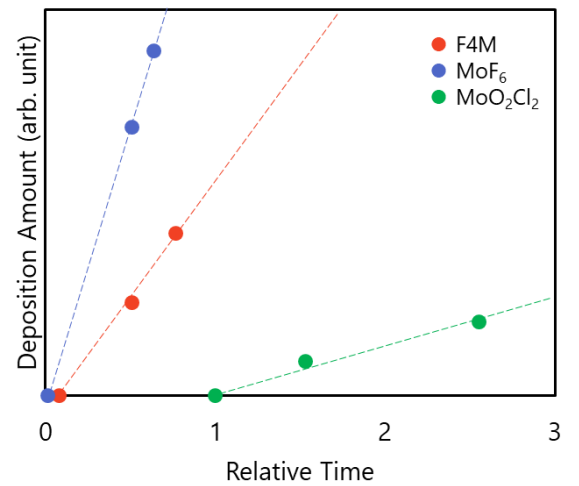


Fig.3 Comparing incubation time for Mo films deposited using different Mo precursors.

Table 1 Comparison of electrical resistivity for Mo films.

Mo precursors	F4M	MoO ₂ Cl ₂	MoCl ₅
Reductants	H ₂		
Electrical resistivity [$\mu\Omega\text{cm}$]	6.9	13 ^[3]	15 ^[3]